

ABSTRACT OF THE DISCLOSURE

Embodiments of the invention generally provide a method for cleaning the bevel edge of a semiconductor substrate, while simultaneously providing protection layer over the production surface of the substrate. The protection layer operates to shield the production surface from contact with any cleaning fluid that is applied to the bevel edge of the substrate. The protection layer may include a thin layer of deionized water applied to the center of the substrate while the substrate is rotated. The method for forming the protection layer generally includes rotating the semiconductor substrate on a substrate support member, dispensing an etching solution onto the bevel of the substrate with a first pivotally mounted fluid dispensing nozzle, and dispensing a protective fluid onto a central portion of the substrate simultaneously with the dispensing of the etching solution with a second pivotally mounted fluid dispensing nozzle.

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